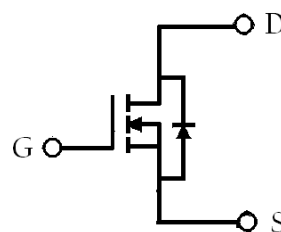
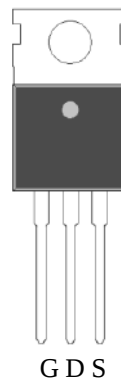


N-Channel Enhancement Mode Power MOSFET

Features:

- Low Gate Charge
- Simple Drive Requirement
- Fast Switching Characteristic
- RoHS compliant package

TO-220



G : Gate D : Drain S : Source

BV_{DSS}	500V
$I_D @ V_{GS}=10V, T_C=25^{\circ}C$	8.5A
$I_D @ V_{GS}=10V, T_C=100^{\circ}C$	5.4A
$R_{DS(on)(TYP)} @ V_{GS}=10V, I_D=4.5A$	0.71 Ω

Ordering Information

Device	Package	Shipping
KWN9N50B	TO-220 (RoHS compliant)	50 pcs/tube, 20 tubes/box, 5 boxes / carton

Absolute Maximum Ratings (T_C=25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage (Note 1)	V _{DS}	500	V
Gate-Source Voltage	V _{GS}	±30	
Continuous Drain Current @T _C =25°C, V _{GS} =10V	I _D	8.5*	A
Continuous Drain Current @T _C =100°C, V _{GS} =10V		5.4*	
Pulsed Drain Current @ V _{GS} =10V (Note 2)	I _{DM}	34*	
Single Pulse Avalanche Energy (Note 3)	E _{AS}	290	mJ
Avalanche Current (Note 2)	I _{AS}	8	A
Repetitive Avalanche Energy (Note 2)	E _{AR}	12.5	mJ
Maximum Temperature for Soldering @ Lead at 0.125 in(3.175mm) from case for 10 seconds	T _L	300	°C
Total Power Dissipation (T _C =25°C)	P _D	134	W
Linear Derating Factor above 25°C		1.07	W/°C
Operating Junction and Storage Temperature	T _J , T _{stg}	-55~+150	°C

*Drain current limited by maximum junction temperature

Note : 1. T_J=+25°C to +150°C.

2. Repetitive rating; pulse width limited by maximum junction temperature.

3. I_{AS}=8A, V_{DD}=50V, L=5mH, R_G=25Ω, starting T_J=+25°C.

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-case, max	R _{θJC}	0.93	°C/W
Thermal Resistance, Junction-to-ambient, max	R _{θJA}	62.5	

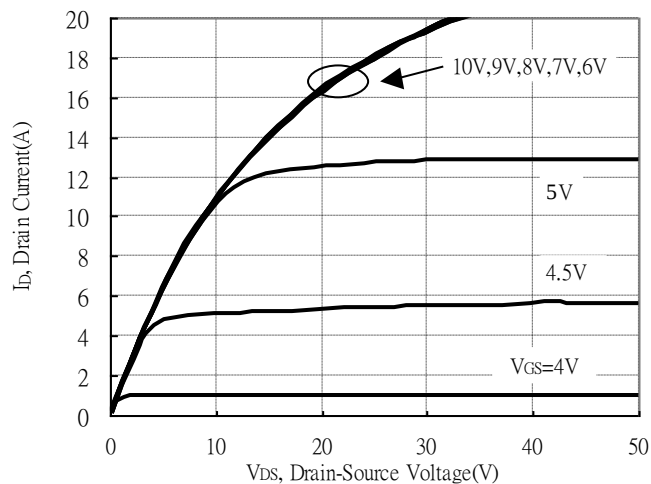
Characteristics (Tj=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	500	-	-	V	V _{GS} =0V, I _D =250μA
V _{GS(th)}	2.0	-	4.0	V	V _{DS} = V _{GS} , I _D =250μA
*G _{FS}	-	8	-	S	V _{DS} =15V, I _D =4A
I _{GSS}	-	-	±100	nA	V _{GS} =±30V, V _{DS} =0V
I _{DSS}	-	-	1	μA	V _{DS} =400V, V _{GS} =0V
*R _{DS(ON)}	-	0.71	0.9	Ω	V _{GS} =10V, I _D =4.5A
Dynamic					
*Q _g	-	26.4	-	nC	I _D =4.5A, V _{DD} =250V, V _{GS} =10V
*Q _{gs}	-	4.8	-		
*Q _{gd}	-	9.9	-		
*t _{d(ON)}	-	14	-	ns	V _{DD} =250V, I _D =4.5A, V _{GS} =10V, R _G =1Ω
*t _r	-	8.8	-		
*t _{d(OFF)}	-	42.6	-		
*t _f	-	7.8	-		
C _{iss}	-	975	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
C _{oss}	-	108	-		
C _{rss}	-	76	-		
Source-Drain Diode					
*I _S	-	-	8	A	
*I _{SM}	-	-	32		
*V _{SD}	-	0.8	1.2	V	I _S =4.5A, V _{GS} =0V
*t _{rr}	-	242	-	ns	V _{GS} =0V, I _F =4.5, dI _F /dt=100A/μs
*Q _{rr}	-	1.5	-	μC	

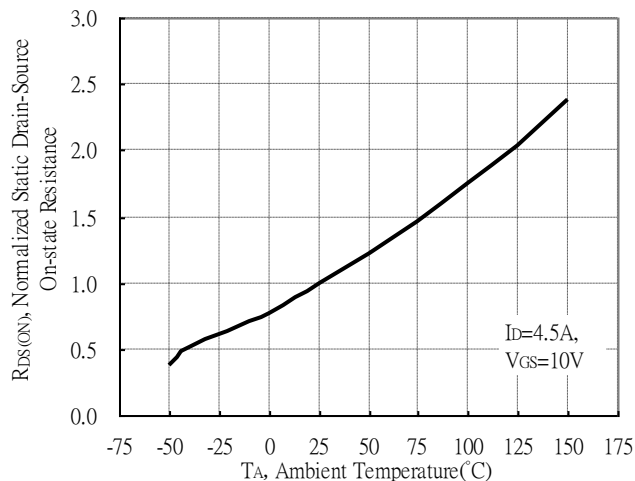
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

Typical Characteristics

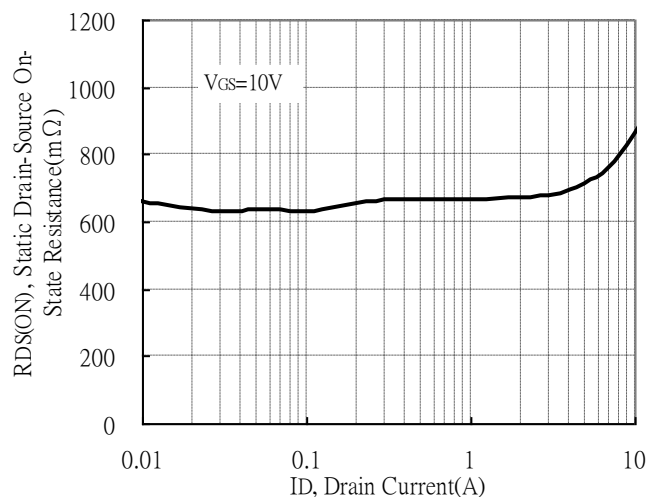
Typical Output Characteristics



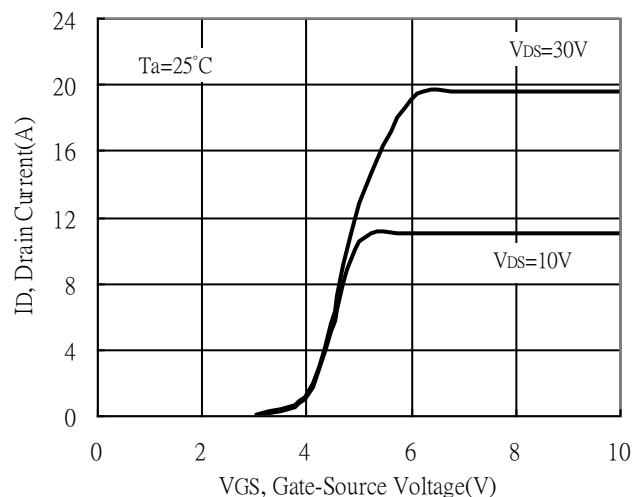
Static Drain-Source On-resistance vs Ambient Temperature



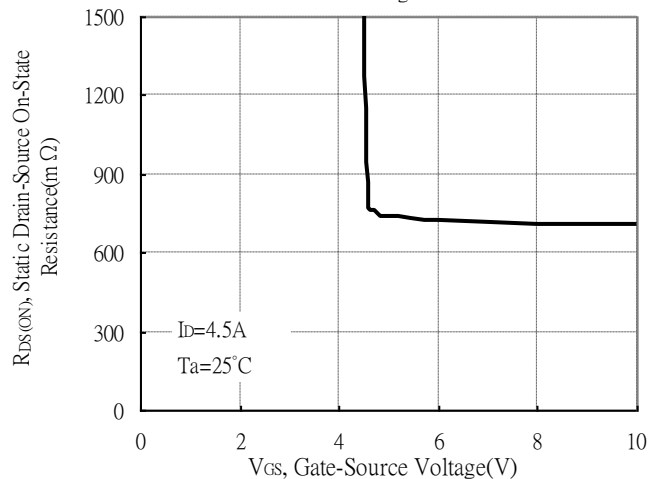
Static Drain-Source On-State resistance vs Drain Current



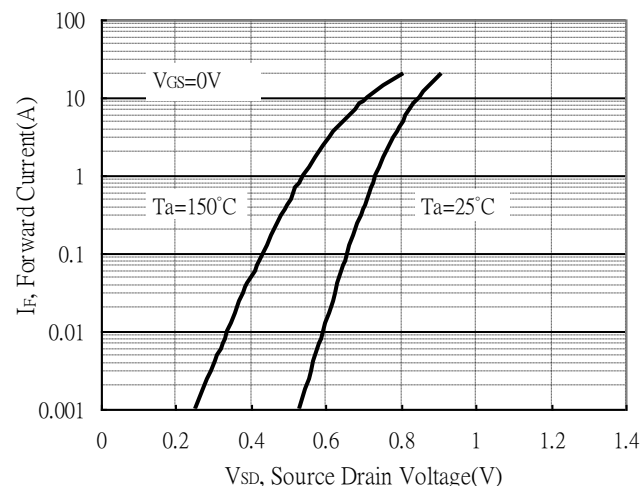
Drain Current vs Gate-Source Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

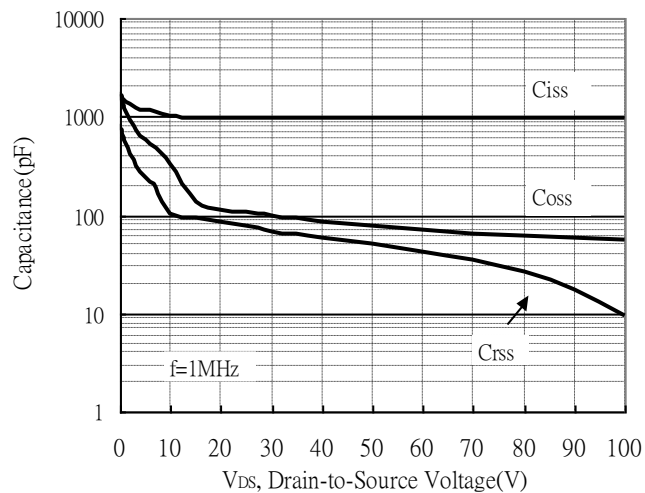


Forward Drain Current vs Source-Drain Voltage

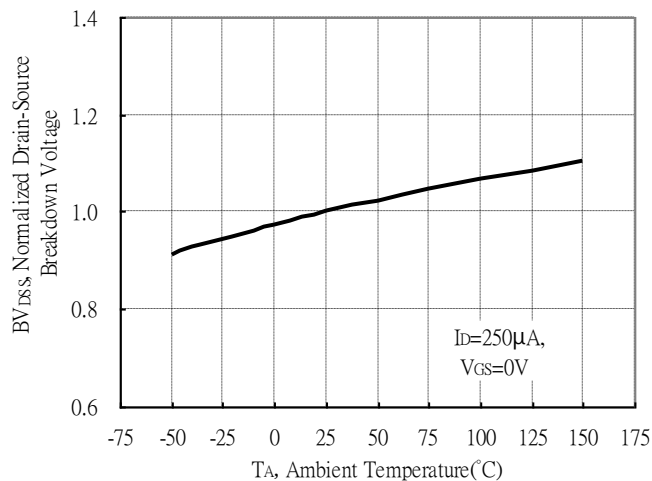


Typical Characteristics(Cont.)

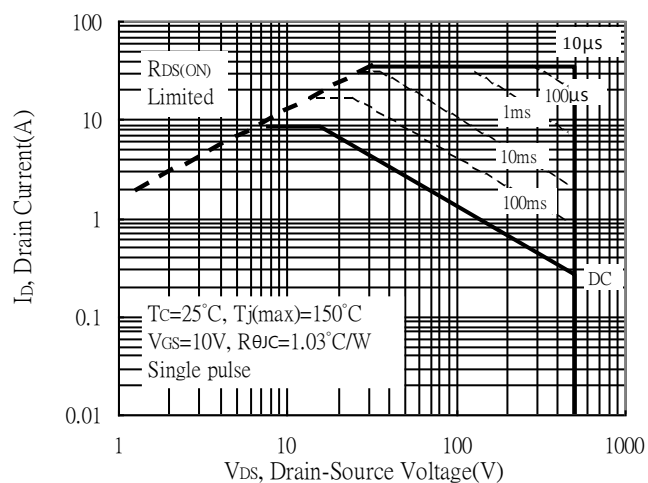
Capacitance vs Reverse Voltage



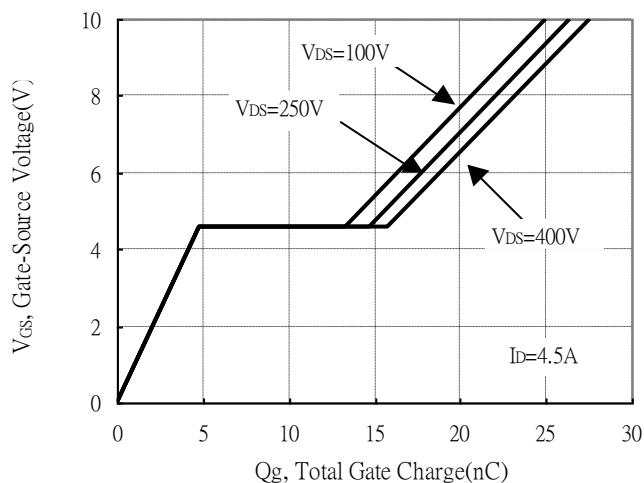
Breakdown Voltage vs Ambient Temperature



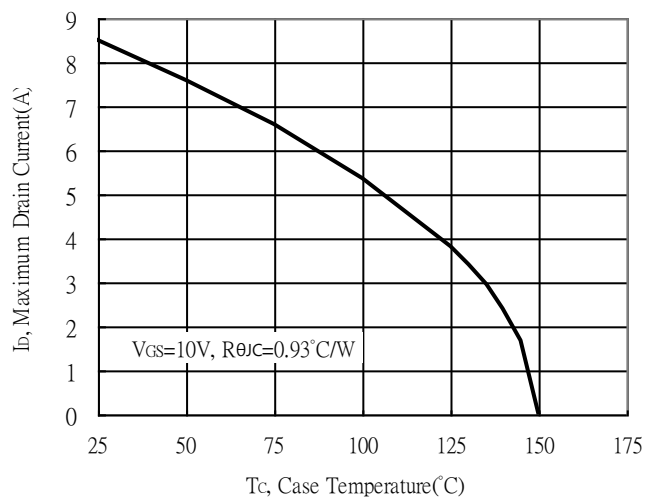
Maximum Safe Operating Area



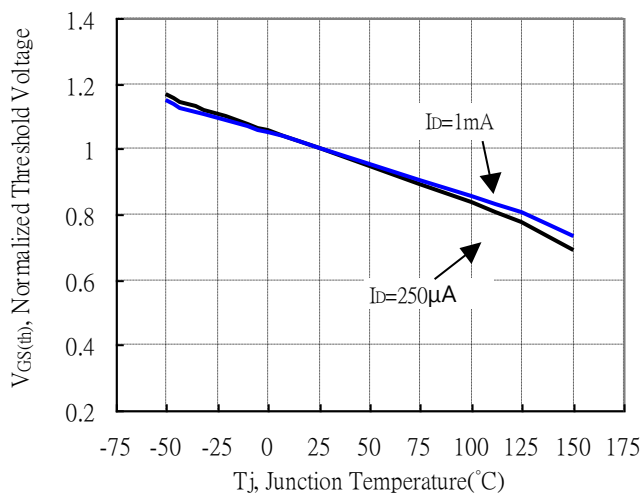
Gate Charge Characteristics



Maximum Drain Current vs Case Temperature

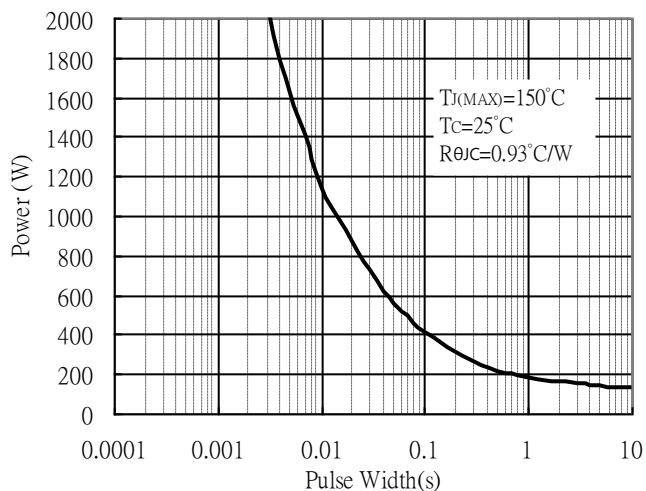


Threshold Voltage vs Junction Temperature

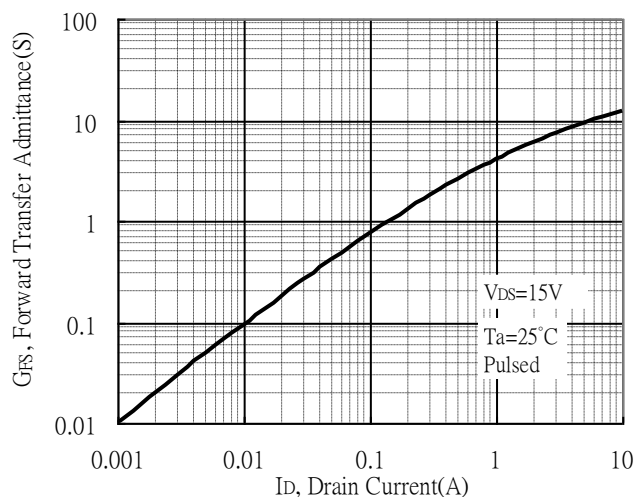


Typical Characteristics(Cont.)

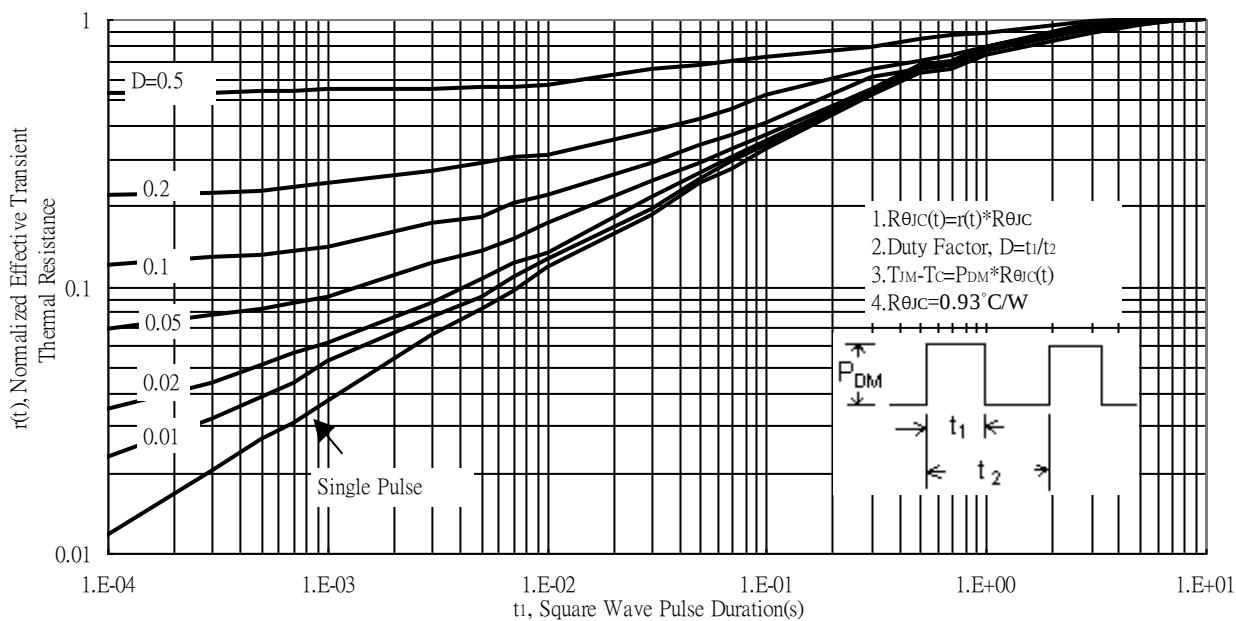
Single Pulse Power Rating, Junction to Case



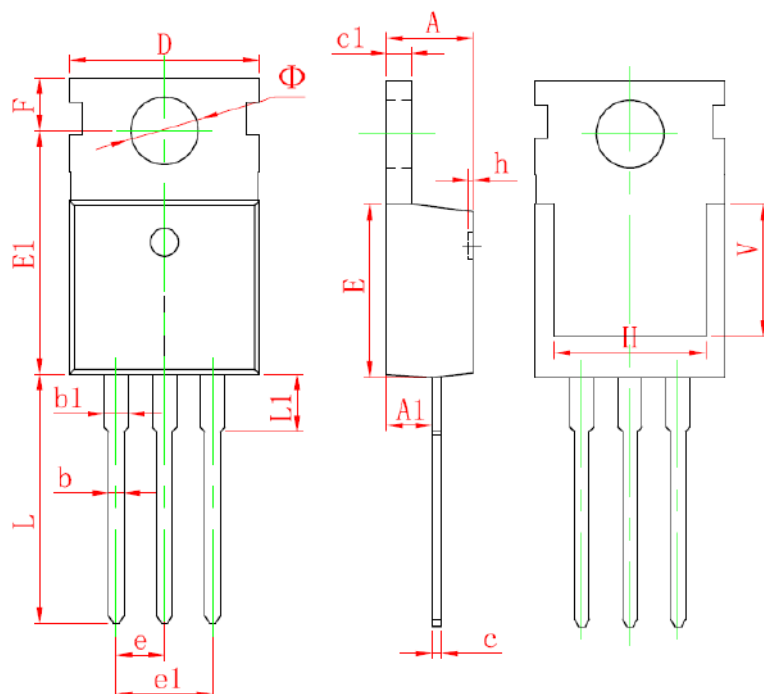
Forward Transfer Admittance vs Drain Current



Transient Thermal Response Curves

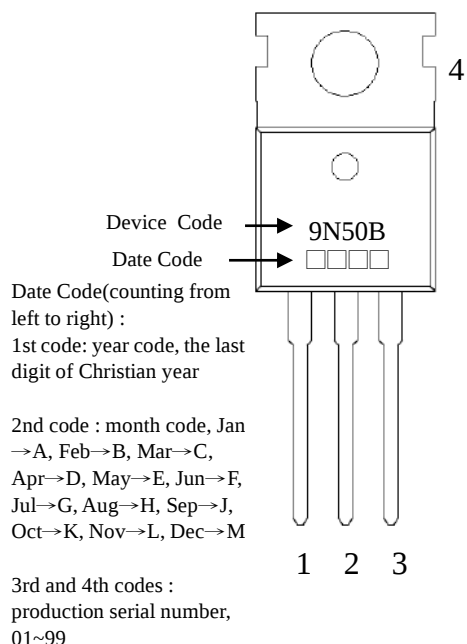


TO-220 Dimension



3-Lead TO-220 Plastic Package

Marking:



Style: Pin 1.Gate 2.Drain 3.Source
 4.Drain

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181	e	2.540*		0.100*	
A1	2.250	2.550	0.089	0.100	e1	4.980	5.180	0.196	0.204
b	0.710	0.910	0.028	0.036	F	2.650	2.950	0.104	0.116
b1	1.170	1.370	0.046	0.054	H	7.900	8.100	0.311	0.319
c	0.330	0.650	0.013	0.026	h	0.000	0.300	0.000	0.012
c1	1.200	1.400	0.047	0.055	L	12.900	13.400	0.508	0.528
D	9.910	10.250	0.390	0.404	L1	2.850	3.250	0.112	0.128
E	8.950	9.750	0.352	0.384	V	7.500	REF	0.295	REF
E1	12.650	12.950	0.498	0.510	Φ	3.400	3.800	0.134	0.150